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FAN7191_F085 High-Current, High and Low Side Gate Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- 4.5A Sourcing and 4.5A Sinking Current Driving Capability
- Common-Mode dV/dt Noise Cancelling Circuit
- Built-in Under-Voltage Lockout for Both Channels
- Matched Propagation Delay for Both Channels
- 3.3V and 5V Input Logic Compatible
- Output In-phase with Input
- Qualified to AEC Q100

Applications

- Advanced Fuel Injection Systems
- Automotive high voltage DC-DC converters
- Starter/Alternator
- Electric Power Steering
- Motor Control (fans, pumps, compressors)
- MOSFET and IGBT driver applications

Description

The FAN7191_F085 is a monolithic high- and low-side gate-drive IC, which can drive high speed MOSFETs and IGBTs that operate up to +600V. It has a buffered output stage with all NMOS transistors designed for high pulse driving capability and minimum cross-conduction.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-drivers under high dV/dt noise circumstances. An advanced level-shift circuit allows high-side gate driver operation up to $V_S = -9.8V$ (typical) for $V_{BS} = 15V$.

The UVLO circuit prevents malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

The high current and low output voltage drop features make this device suitable for controlling direct injection actuators and for use in many automotive DC-DC converter and motor control applications.

8-SOP



Figure 1. Package Options

Ordering Information

Part Number	Operating Temperature Range	Package	Eco Status Packing M	
FAN7191MX_F085	-40°C to +125°C	8-SOP	RoHS	Tape & Reel



For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Typical Application Circuit 15V R_{boot} D_{boot} Up to 600V HIN V_{B} Controller Q_1 R_1 но (2 LIN R_2 C_{boot} COM V_{S} LO V_{DD} (Q_2 R_3 Load R_4 Figure 2. Half-Bridge Application Circuit (8-SOP)

Internal Block Diagram

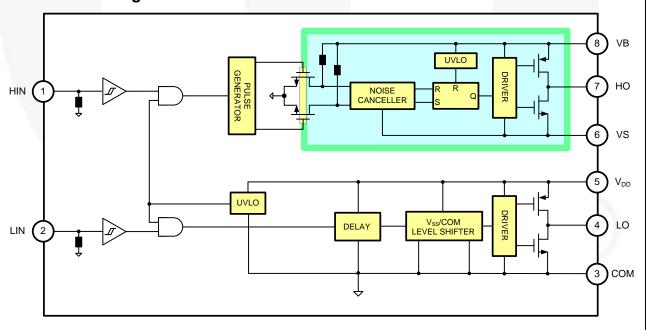


Figure 3. Functional Block Diagram (8-SOP)

Pin Assignment

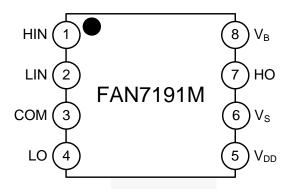


Figure 4. Pin Assignments (Top View)

Pin Definitions

8-Pin	Name	Description	
1	HIN	Logic Input for High-Side Gate Driver Output	
2	LIN	Logic Input for Low-Side Gate Driver Output	
3	СОМ	Low-side Driver Return	
4	LO	Low-Side Driver Output	
5	V _{DD}	Low-Side and Logic Power Supply Voltage	
6	Vs	High-Side Floating Supply Return	
7	НО	High-Side Driver Output	
8	V _B	High-Side Floating Supply	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

TA = 25°C, unless otherwise specified. V_B , V_{DD} and V_{IN} are referenced to COM for FAN7191M (8-SOP).

Symbol	Parameter		Min.	Max.	Unit		
Vs	High-side offset voltage VS			VB-25	VB+0.3	V	
V _B	High-side floating supply voltage VB			-0.3	625	V	
V _{HO}		High-side floatir	ng output voltage		VS-0.3	VB+0.3	V
V _{DD}		Low-side and logic-	fixed supply voltage	е	-0.3	25	V
V _{IN}		Logic Input volta	ge (HIN, LIN, EN)		-0.3	VDD+0.3	V
V _{LO}		Low-Side Out	put Voltage LO	1/4	COM-0.3	VDD+0.3	V
t _{pulse}	Minimum Pulse Width ⁽⁴⁾			80		ns	
d _{VS/dt}	Allowable offset voltage slew rate				50	V/ns	
P _D ⁽¹⁾⁽²⁾⁽³⁾	Power dissipa	ation		8-SOP		0.625	W
□ЈА	Thermal Resi	stance, junction-to-amb	pient	8-SOP		200	°C/W
TJ	Junction temp	perature				+150	°C
Ts	Storage temperature			-55	+150	°C	
ESD	Electrostatic Discharge	Human Body Model, A	NSI/ESDA/JEDEC	JS-001-2012		3000	V
202	Capability	Charged Device Mode	el, JESD22-C101			2000	v

Notes:

- 1. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 2. Refer to the following standards:
 - JESD51-2: Integral circuits thermal test method environmental conditions natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages
- 3. Do not exceed P_D under any circumstances.
- 4. Minimum input pulse which is guaranteed to produce an output pulse.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings. V_{DD} is referenced to COM for FAN7191M (8-SOP).

Symbol	Parameter	Min.	Max.	Unit
V _B	High-side floating supply voltage	V _S +10	V _S +22	V
Vs	High-side Floating Supply Offset Voltage	6-V _{DD}	600	V
V_{HO}	High-side Output Voltage	Vs	V _B	V
V_{DD}	Low-side and Logic Supply voltage	5.6	20	V
V_{LO}	Low-side output voltage	COM	V_{DD}	V
V _{IN}	Logic input voltage (HIN, LIN)	COM	V_{DD}	V
COM	Power Ground	V _{SS} -0.5	V _{SS} +0.5	V
T _A	Ambient Temperature	-40	+125	°C

Electrical Characteristics

 V_{BIAS} (V_{DD} , V_{BS}) = 15.0V, V_S = COM, T_A = 25°C, unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to COM and are applicable to the respective input signals HIN and LIN. The V_O and I_O parameters are referenced to COM. V_S and GND and are applicable to the respective outputs HO and LO.

Symbol	Characteristic	Condition	Min.	Тур.	Max.	Unit
POWER S	UPPLY SECTION (V _{DD} and V _{BS})		u.			
V _{DDUV+} V _{BSUV+}	V _{DD} and V _{BS} Supply Under-Voltage Positive-going Threshold		7.8	8.8	9.8	
V _{DDUV} - V _{BSUV} -	V _{DD} and V _{BS} Supply Under-Voltage Negative Going Threshold		7.2	8.3	9.1	٧
V _{DDHYS}	V _{DD} supply under-voltage lockout hysteresis			0.5		
I_{LK}	Offset Supply Leakage Current	$V_B = V_S = 600V$			50	
I_{QBS}	Quiescent V _{BS} Supply Current	V _{IN} = 0V or 5V		45	110	μΑ
I_{QDD}	Quiescent V _{DD} Supply Current	V _{IN} = 0V or 5V		75	150	
I _{PBS}	Operating V _{BS} Supply Current	f _{IN} = 20kHz, rms value		400	800	
I _{PDD}	Operating V _{DD} Supply Current	f _{IN} = 20kHz, rms value		400	800	μΑ
LOGIC INF	PUT SECTION (HIN, LIN, EN)					
V_{IH}	Logic "1" Input Voltage		2.5			\ \
V_{IL}	Logic "0" Input Voltage				1.2	V
I _{IN+}	Logic "1" Input Bias Current (HIN/LIN)	$V_{IN} = 5V$	V	25	50	
I _{IN-}	Logic "0" Input Bias Current (HIN/LIN)	$V_{IN} = 0V$		1.0	2.0	μА
R _{IN}	Input Pull-down Resistance		100	200		kΩ
GATE DRI	VER OUTPUT SECTION (HO, LO)					
V _{OH}	High-level Output Voltage, V _{BIAS} -V _O	No Load			1.35	V
V _{OL}	Low-level Output Voltage, Vo	No Load			35	mV
I _{O+}	Output HIGH, Short-circuit Pulsed Current	V _O =0V, V _{IN} =5V with PW<10μs	3.5	4.5		А
I _{O-}	Output LOW Short-circuit Pulsed Current	$V_O=15V$, $V_{IN}=0V$ with PW<10 μ s	3.5	4.5		
Vs	Allowable Negative V _S Pin Voltage for HIN Signal Propagation to HO	4		-9.8	-7.0	٧

Note:

Dynamic Electrical Characteristics

V_{BIAS} (V_{DD}, V_{BS}) = 15.0V, V_S = COM = 0V, T_A = 25°C, C_{LOAD}=1000pF unless otherwise specified.

Symbol	Characteristic	Condition	Min.	Тур.	Max.	Unit
ton	Turn-on Propagation Delay	V _S =0V		140	200	ns
t _{off}	Turn-off Propagation Delay	V _S =0V		140	200	ns
MT	Delay Matching				55	ns
t _r	Turn-off Rise Time			25	50	ns
t _f	Turn-off Fall Time			25	50	ns

^{5.} This parameter guaranteed by design.

Typical Characteristics

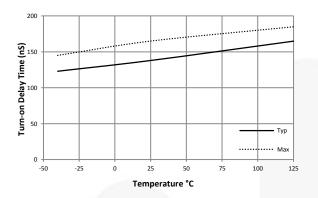
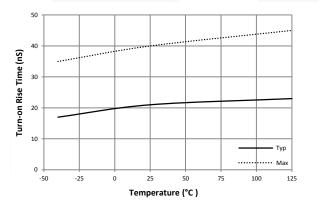


Figure 7. Turn-on Propagation Delay vs. Temperature

Figure 8. Turn-off Propagation Delay vs. Temperature



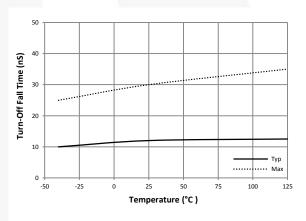
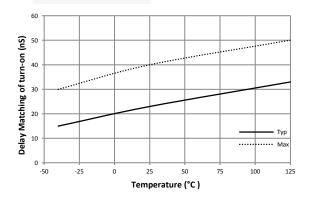


Figure 9. Turn-on Rise Time vs. Temperature

Figure 10. Turn-off Fall Time vs. Temperature



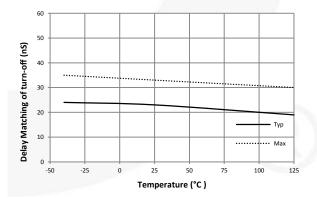


Figure 11. Turn-on Delay Matching vs. Temperature

Figure 12. Turn-off Delay Matching vs. Temperature

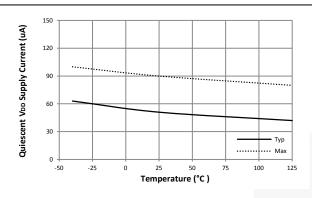


Figure 13. Quiescent V_{DD} Supply Current vs. Temperature

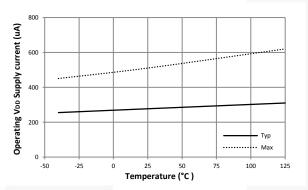


Figure 15. Operating V_{DD} Supply Current vs. Temperature

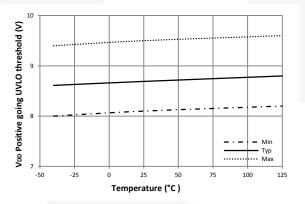


Figure 17. V_{DD} UVLO+ vs. Temperature

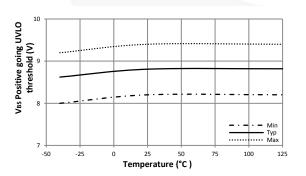


Figure 19. V_{BS} UVLO+ vs. Temperature

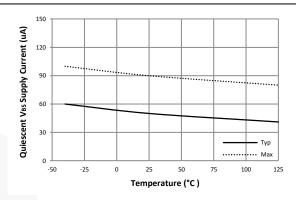


Figure 14. Quiescent V_{BS} Supply Current vs. Temperature

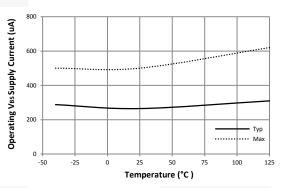


Figure 16. Operating V_{BS} Supply Current vs. Temperature

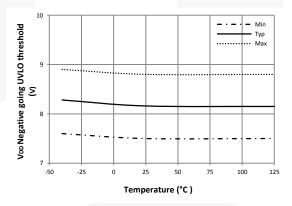


Figure 18. V_{DD} UVLO- vs. Temperature

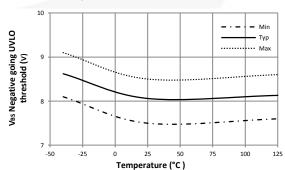


Figure 20. V_{BS} UVLO- vs. Temperature

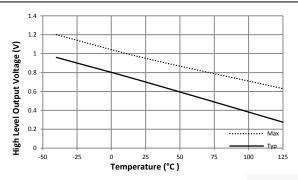


Figure 21. High-Level Output Voltage vs. Temperature

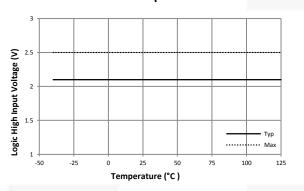


Figure 23. Logic High Input Voltage

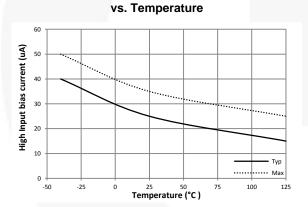


Figure 25. Logic "1" Input Bias Current vs.
Temperature

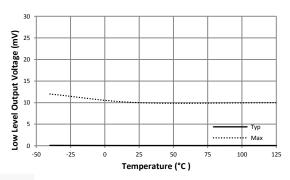


Figure 22. Low-Level Output Voltage vs. Temperature

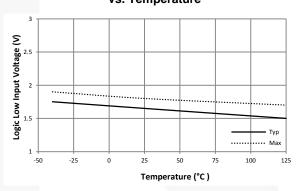


Figure 24. Logic Low Input Voltage

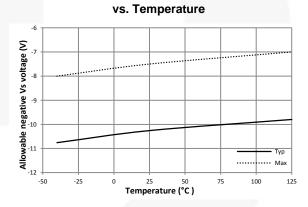


Figure 26. Allowable Negative V_S Voltage vs. Temperature

Switching Time Definitions

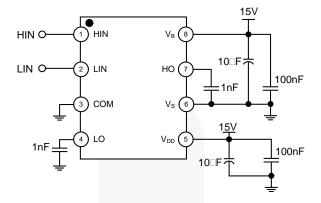


Figure 27. Switching Time Test Circuit (8-SOP)

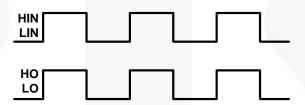


Figure 28. Input/Output Timing Diagram

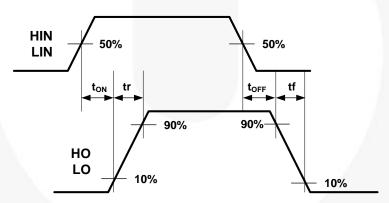


Figure 29. Switching Time Waveform Definitions

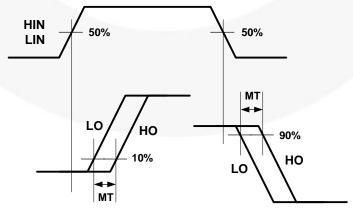
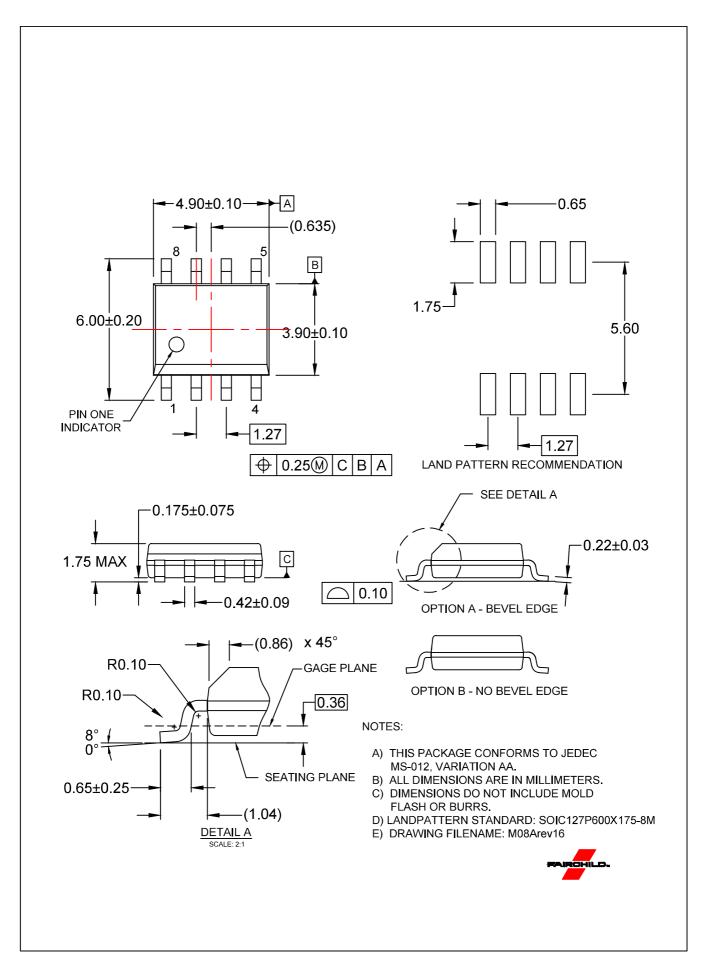


Figure 30. Delay Matching Waveform Definition



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